



**THE DATASHEET OF  
SZNUD3112LT1G**



# Integrated Relay, Inductive Load Driver

## NUD3112

This device is used to switch inductive loads such as relays, solenoids incandescent lamps, and small DC motors without the need of a free-wheeling diode. The device integrates all necessary items such as the MOSFET switch, ESD protection, and Zener clamps. It accepts logic level inputs thus allowing it to be driven by a large variety of devices including logic gates, inverters, and microcontrollers.

### Features

- Provides a Robust Driver Interface Between D.C. Relay Coil and Sensitive Logic Circuits
- Optimized to Switch Relays of 12 V Rail
- Capable of Driving Relay Coils Rated up to 6.0 W at 12 V
- Internal Zener Eliminates the Need of Free-Wheeling Diode
- Internal Zener Clamp Routes Induced Current to Ground for Quieter Systems Operation
- Low  $V_{DS(ON)}$  Reduces System Current Drain
- These Devices is Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

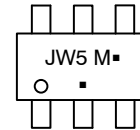
### Typical Applications

- Telecom: Line Cards, Modems, Answering Machines, FAX
- Computers and Office: Photocopiers, Printers, Desktop Computers
- Consumer: TVs and VCRs, Stereo Receivers, CD Players, Cassette Recorders
- Industrial: Small Appliances, Security Systems, Automated Test Equipment, Garage Door Openers



SC-74  
CASE 318F  
STYLE 7

### MARKING DIAGRAM



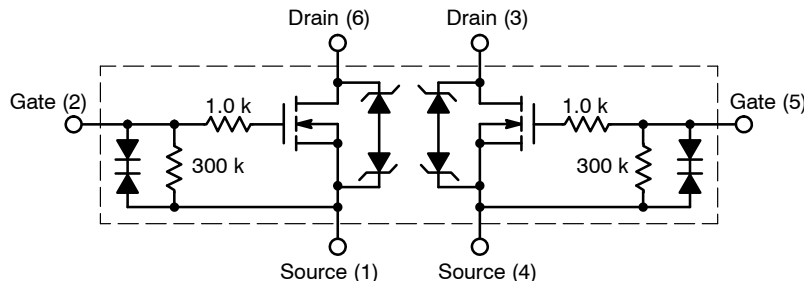
JW5 = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NUD3112DMT1G	SC-74 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

### INTERNAL CIRCUIT DIAGRAMS



# NUD3112

## MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Rating	Value	Unit
$V_{DSS}$	Drain to Source Voltage – Continuous	14	$V_{dc}$
$V_{GS}$	Gate to Source Voltage – Continuous	6	$V_{dc}$
$I_D$	Drain Current – Continuous	500	mA
$E_z$	Single Pulse Drain-to-Source Avalanche Energy ( $T_{Jinitial} = 25^\circ\text{C}$ )	50	mJ
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_A$	Operating Ambient Temperature	-40 to 85	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-65 to +150	$^\circ\text{C}$
$P_D$	Total Power Dissipation (Note 1) Derating Above $25^\circ\text{C}$	1.8	$\text{mW}/^\circ\text{C}$
$P_D$	Total Power Dissipation (Note 1) Derating Above $25^\circ\text{C}$	3.0	$\text{mW}/^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient (Note 1)	329	$^\circ\text{C}/\text{W}$
ESD	Human Body Model (HBM) According to EIA/JESD22/A114	2000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Mounted onto minimum pad board.

## TYPICAL ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Characteristic	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

$V_{BRDSS}$	Drain to Source Sustaining Voltage (Internally Clamped) ( $I_D = 10\text{ mA}$ )	14	16	17	V
$BV_{GSO}$	$I_g = 1.0\text{ mA}$	-	-	8	V
$I_{DSS}$	Drain to Source Leakage Current ( $V_{DS} = 12\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_A = 25^\circ\text{C}$ ) ( $V_{DS} = 12\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_A = 85^\circ\text{C}$ )	-	-	20 40	$\mu\text{A}$
$I_{GSS}$	Gate Body Leakage Current ( $V_{GS} = 3.0\text{ V}$ , $V_{DS} = 0\text{ V}$ ) ( $V_{GS} = 5.0\text{ V}$ , $V_{DS} = 0\text{ V}$ )	-	-	35 65	$\mu\text{A}$

### ON CHARACTERISTICS

$V_{GS(th)}$	Gate Threshold Voltage ( $V_{GS} = V_{DS}$ , $I_D = 1.0\text{ mA}$ ) ( $V_{GS} = V_{DS}$ , $I_D = 1.0\text{ mA}$ , $T_A = 85^\circ\text{C}$ )	0.8 0.8	1.2 -	1.4 1.4	V
$R_{DS(on)}$	Drain to Source On-Resistance ( $I_D = 250\text{ mA}$ , $V_{GS} = 3.0\text{ V}$ ) ( $I_D = 500\text{ mA}$ , $V_{GS} = 3.0\text{ V}$ ) ( $I_D = 500\text{ mA}$ , $V_{GS} = 5.0\text{ V}$ ) ( $I_D = 500\text{ mA}$ , $V_{GS} = 3.0\text{ V}$ , $T_A = 85^\circ\text{C}$ ) ( $I_D = 500\text{ mA}$ , $V_{GS} = 5.0\text{ V}$ , $T_A = 85^\circ\text{C}$ )	- - - - -	- - - - -	1.2 1.3 0.9 1.3 0.9	$\Omega$
$I_{DS(on)}$	Output Continuous Current ( $V_{DS} = 0.25\text{ V}$ , $V_{GS} = 3.0\text{ V}$ ) ( $V_{DS} = 0.25\text{ V}$ , $V_{GS} = 3.0\text{ V}$ , $T_A = 85^\circ\text{C}$ )	300 200	400 -	- -	mA
$g_{FS}$	Forward Transconductance ( $V_{OUT} = 12.0\text{ V}$ , $I_{OUT} = 0.25\text{ A}$ )	350	490	-	mmhos

# NUD3112

## TYPICAL ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (continued)

Symbol	Characteristic	Min	Typ	Max	Unit
<b>DYNAMIC CHARACTERISTICS</b>					
$C_{iss}$	Input Capacitance ( $V_{DS} = 12\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 10\text{ kHz}$ )	-	23	-	pF
$C_{oss}$	Output Capacitance ( $V_{DS} = 12\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 10\text{ kHz}$ )	-	30	-	pF
$C_{rss}$	Transfer Capacitance ( $V_{DS} = 12.0\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 10\text{ kHz}$ )	-	7	-	pF

## SWITCHING CHARACTERISTICS

Symbol	Characteristic	Min	Typ	Max	Unit
$t_{PHL}$	Propagation Delay Times: High to Low Propagation Delay; Figure 1 ( $V_{DS} = 12\text{ V}$ , $V_{GS} = 5.0\text{ V}$ ) Low to High Propagation Delay; Figure 1 ( $V_{DS} = 12\text{ V}$ , $V_{GS} = 5.0\text{ V}$ )	-	21	-	nS
$t_{PLH}$		-	91	-	nS
$t_f$	Transition Times: Fall Time; Figure 1 ( $V_{DS} = 12\text{ V}$ , $V_{GS} = 5.0\text{ V}$ ) Rise Time; Figure 1 ( $V_{DS} = 12\text{ V}$ , $V_{GS} = 5.0\text{ V}$ )	-	36	-	nS
$t_r$		-	61	-	nS

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

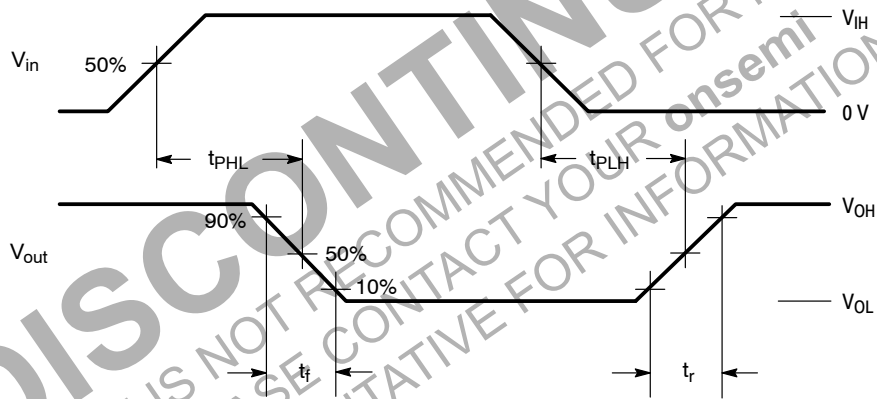


Figure 1. Switching Waveforms

TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$  UNLESS OTHERWISE SPECIFIED)

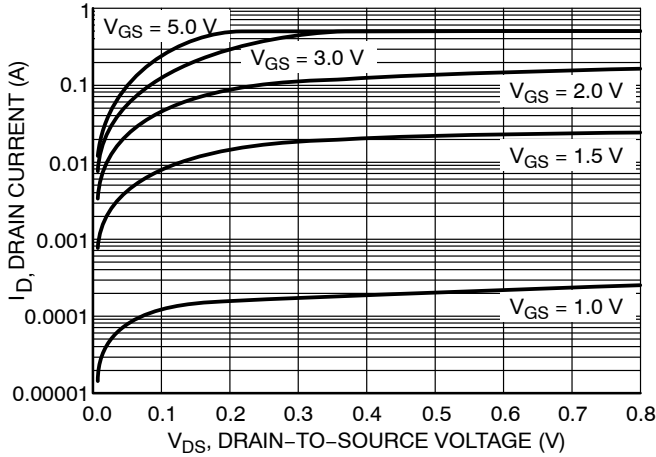


Figure 2. Output Characteristics

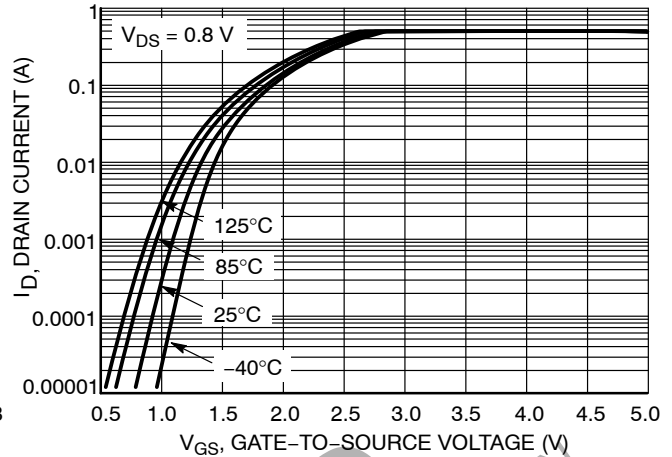


Figure 3. Transfer Function

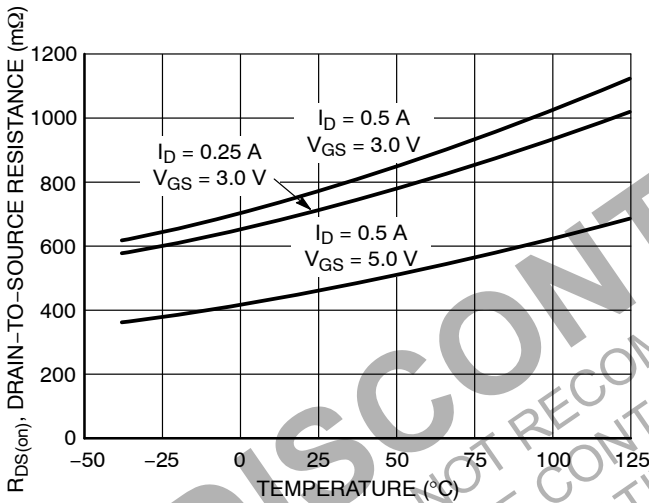


Figure 4. On-Resistance Variation vs. Temperature

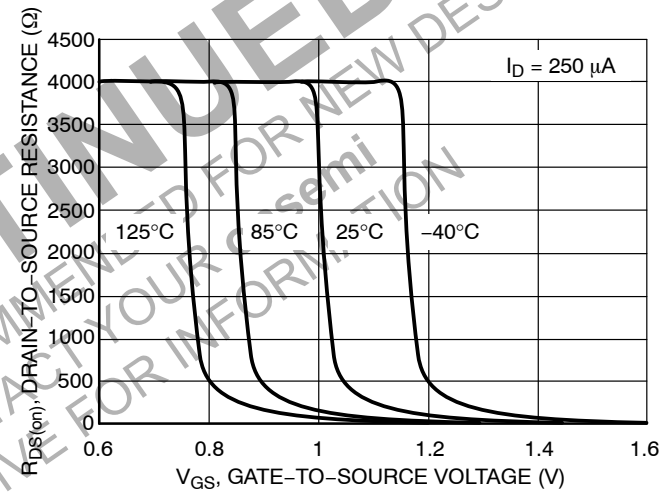


Figure 5.  $R_{DS(ON)}$  Variation vs. Gate-to-Source Voltage

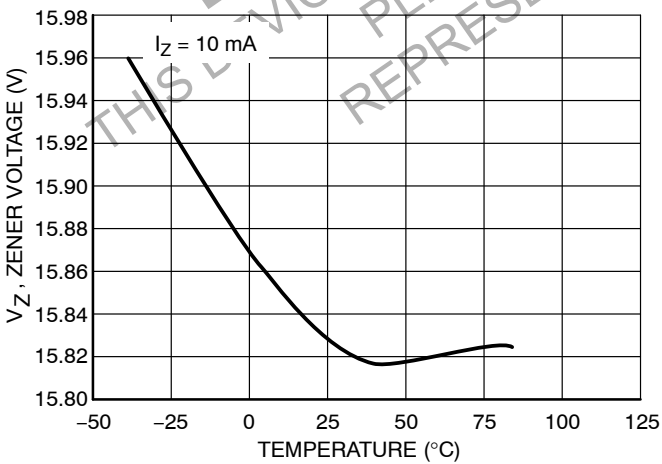


Figure 6. Zener Voltage vs. Temperature

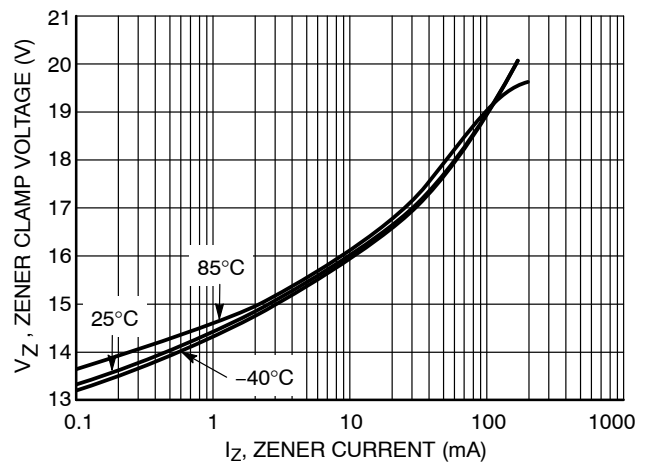
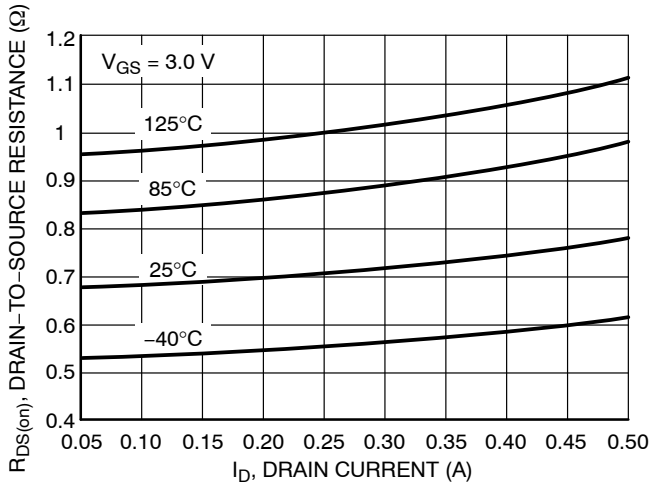


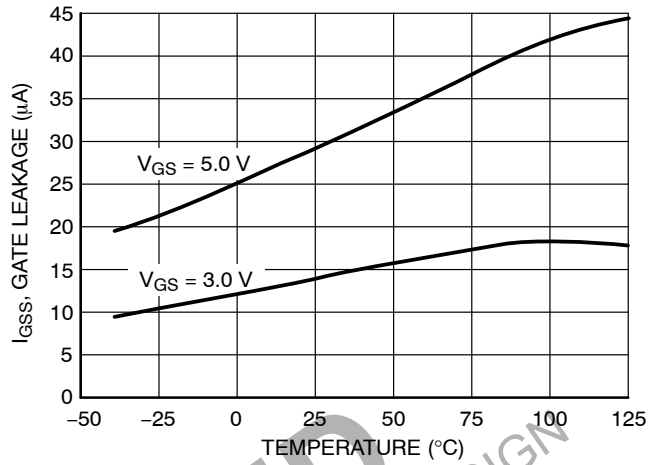
Figure 7. Zener Clamp Voltage vs. Zener Current

# NUD3112

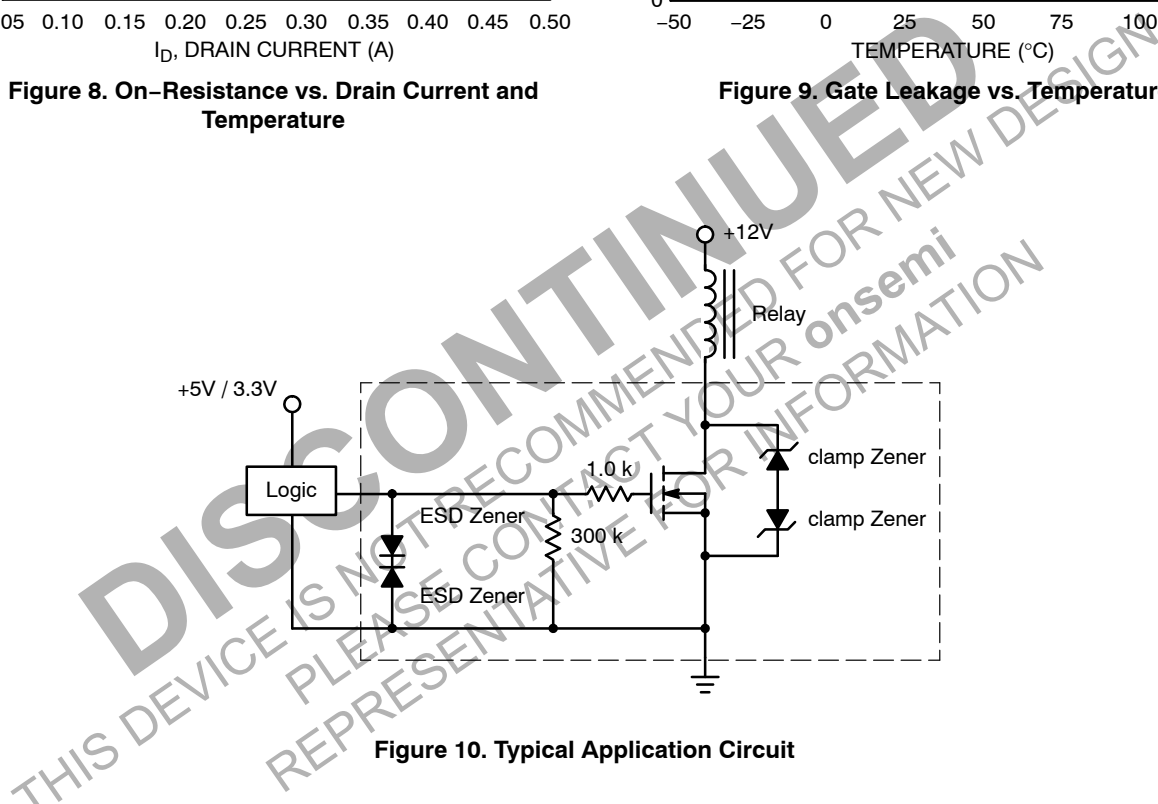
## TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED) (continued)



**Figure 8. On-Resistance vs. Drain Current and Temperature**



**Figure 9. Gate Leakage vs. Temperature**



**Figure 10. Typical Application Circuit**

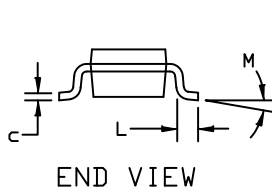
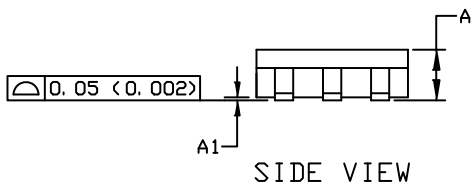
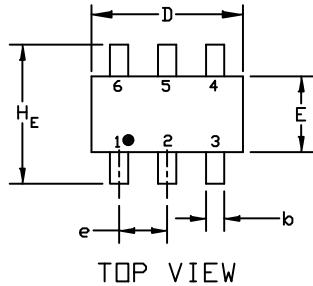
# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



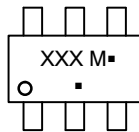
SCALE 2:1

**SC-74**  
CASE 318F  
ISSUE P

DATE 07 OCT 2021



### GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

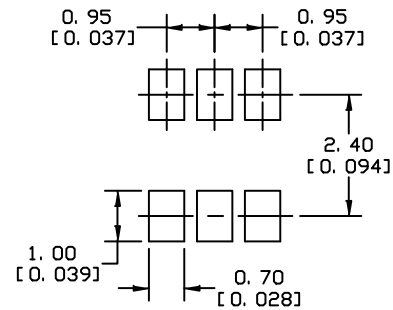
(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994
2. CONTROLLING DIMENSION: INCHES
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
HE	2.50	2.75	3.00	0.099	0.108	0.118
L	0.20	0.40	0.60	0.008	0.016	0.024
M	0*	---	10*	0*	---	10*



\* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

### SOLDERING FOOTPRINT

#### STYLE 1:

- PIN 1. CATHODE
- 2. ANODE
- 3. CATHODE
- 4. CATHODE
- 5. ANODE
- 6. CATHODE

#### STYLE 2:

- PIN 1. NO CONNECTION
- 2. COLLECTOR
- 3. EMITTER
- 4. NO CONNECTION
- 5. COLLECTOR
- 6. BASE

#### STYLE 3:

- PIN 1. EMITTER 1
- 2. BASE 1
- 3. COLLECTOR 2
- 4. EMITTER 2
- 5. BASE 2
- 6. COLLECTOR 1

#### STYLE 4:

- PIN 1. COLLECTOR 2
- 2. EMITTER 1/EMITTER 2
- 3. COLLECTOR 1
- 4. EMITTER 3
- 5. BASE 1/BASE 2/COLLECTOR 3
- 6. BASE 3

#### STYLE 5:

- PIN 1. CHANNEL 1
- 2. ANODE
- 3. CHANNEL 2
- 4. CHANNEL 3
- 5. CATHODE
- 6. CHANNEL 4

#### STYLE 6:

- PIN 1. CATHODE
- 2. ANODE
- 3. CATHODE
- 4. CATHODE
- 5. CATHODE
- 6. CATHODE

#### STYLE 7:

- PIN 1. SOURCE 1
- 2. GATE 1
- 3. DRAIN 2
- 4. SOURCE 2
- 5. GATE 2
- 6. DRAIN 1

#### STYLE 8:

- PIN 1. EMITTER 1
- 2. BASE 2
- 3. COLLECTOR 2
- 4. EMITTER 2
- 5. BASE 1
- 6. COLLECTOR 1

#### STYLE 9:

- PIN 1. EMITTER 2
- 2. BASE 2
- 3. COLLECTOR 1
- 4. EMITTER 1
- 5. BASE 1
- 6. COLLECTOR 2

#### STYLE 10:

- PIN 1. ANODE/CATHODE
- 2. BASE
- 3. EMITTER
- 4. COLLECTOR
- 5. ANODE
- 6. CATHODE

#### STYLE 11:

- PIN 1. EMITTER
- 2. BASE
- 3. ANODE/CATHODE
- 4. ANODE
- 5. CATHODE
- 6. COLLECTOR

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